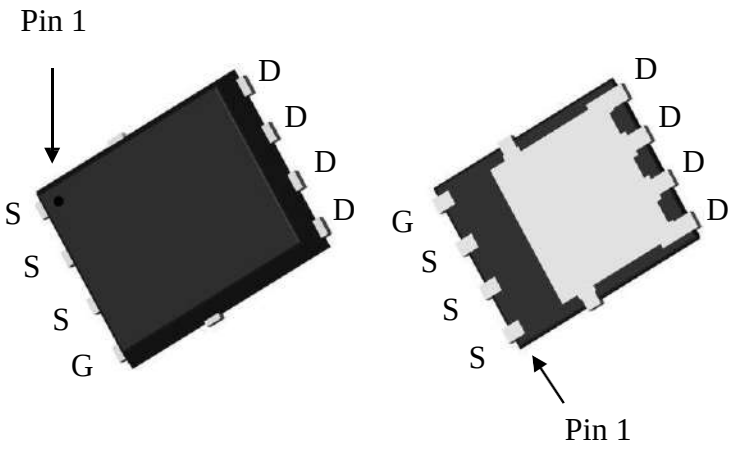
P-Channel Enhancement Mode Power MOSFET

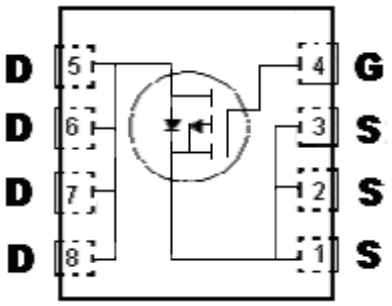
Features:

- Single Drive Requirement
- Low On-resistance
- Fast Switching Characteristic
- Pb-free lead plating and Halogen-free package

DFN5x6



BV_{DSS}		-20V
I_D@V_{GS}=-4.5V, T_C=25°C		-85.5A
I_D@V_{GS}=-4.5V, T_A=25°C		-27A
$R_{DSON(TYP)}$	V_{GS}=-4.5V, I_D=-20A	2.0mΩ
	V_{GS}=-2.5V, I_D=-20A	2.6mΩ



G：Gate D：Drain S：Source

Ordering Information

Device	Package	Shipping
KWA2D0P02H8	DFN5x6 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	10s	Steady State	Unit
Drain-Source Voltage		V_{DS}	-20		V
Gate-Source Voltage		V_{GS}	±8		
Continuous Drain Current @ T_C=25°C, V_{GS}=-4.5V (Note1)		I_D	-85.5 (silicon limit)		A
Continuous Drain Current @ T_C=100°C, V_{GS}=-4.5V (Note1)			-54.0 (silicon limit)		
Continuous Drain Current @ T_C=25°C, V_{GS}=-4.5V (Note1)			-43 (package limit)		
Continuous Drain Current @ T_A=25°C, V_{GS}=-4.5V (Note2)		I_{DSM}	-27	-17.5	
Continuous Drain Current @ T_A=70°C, V_{GS}=-4.5V (Note2)			-21.6	-14.0	
Pulsed Drain Current (Note3)		I_{DM}	-287		
Avalanche Current @ L=0.1mH		I_{AS}	-82		
Avalanche Energy @ L=0.5mH, I_D=-50A, V_{DD}=-15V (Note4)		E_{AS}	625		mJ
Total Power Dissipation	T_C=25℃ (Note1)	P_D	50		W
	T_C=100℃ (Note1)		20		
	T_A=25°C (Note2)	P_{DSM}	5.0	2.1	
	T_A=70°C (Note2)		3.2	1.3	
Operating Junction and Storage Temperature Range		Tj, Tstg	-55~+150		°C

Thermal Data

Parameter		Symbol	Typical	Maximum	Unit
Thermal Resistance, Junction-to-case		$R_{th,j-c}$	2	2.5	°C/W
Thermal Resistance, Junction-to-ambient (Note2)	t≤10s	$R_{th,j-a}$	18	25	
	Steady State		50	60	

Note : 1.The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

2. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

3. Pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.

4. 100% tested by conditions of L=0.1mH, V_{GS}=-10V, I_{AS}=-40A, V_{DD}=-15V

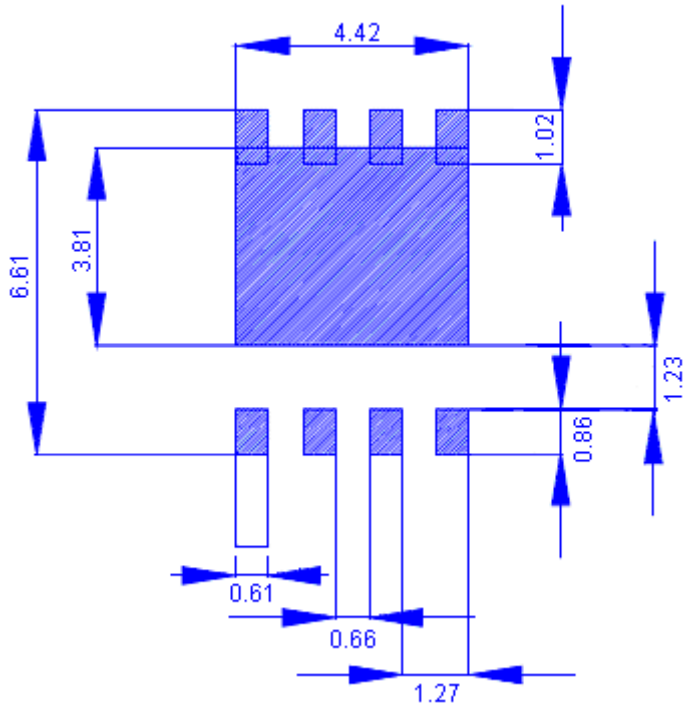
Characteristics (T_C=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	-20	-	-	V	V_{GS}=0V, I_D=-250μA
$V_{GS(th)}$	-0.5	-	-1.2		V_{DS} = V_{GS}, I_D=-250μA
G_{FS} *1	-	82.8	-	S	V_{DS} =-10V, I_D=-20A
I_{GSS}	-	-	±100	nA	V_{GS}=±8V, V_{DS}=0V
I_{DSS}	-	-	-1	μA	V_{DS} =-16V, V_{GS} =0V
	-	-	-25		V_{DS} =-16V, V_{GS} =0V, Tj=125°C

R_{DSON} *1	-	2.0	2.8	mΩ	V_{GS} =-4.5V, I_D=-20A
	-	2.6	4.5		V_{GS} =-2.5V, I_D=-20A
Dynamic *4					
Ciss	-	19369	-	pF	V_{DS}=-20V, V_{GS}=0V, f=1MHz
Coss	-	1442	-		
Crss	-	550	-		
Qg *1, 2	-	218	-	nC	V_{DS}=-15V, V_{GS}=-4.5V, I_D=-20A
Qgs *1, 2	-	30	-		
Qgd *1, 2	-	81	-		
$t_{d(ON)}$ *1, 2	-	30.8	-	ns	V_{DS}=-10V, I_D=-25A, V_{GS}=-4.5V, R_G=1Ω
tr *1, 2	-	29	-		
$t_{d(OFF)}$ *1, 2	-	294	-		
t_f *1, 2	-	114	-		
Rg	-	1.8	-	Ω	f=1MHz
Source-Drain Diode					
V_{SD} *1	-	-0.8	-1.2	V	I_S=-20A, V_{GS}=0V
trr	-	42	-	ns	I_F=-20A, dI_F/dt=100A/μs
Qrr	-	47	-	nC	

Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
*2.Independent of operating temperature
*3.Pulse width limited by maximum junction temperature.
*4.Guaranteed by design, not subject to production testing.

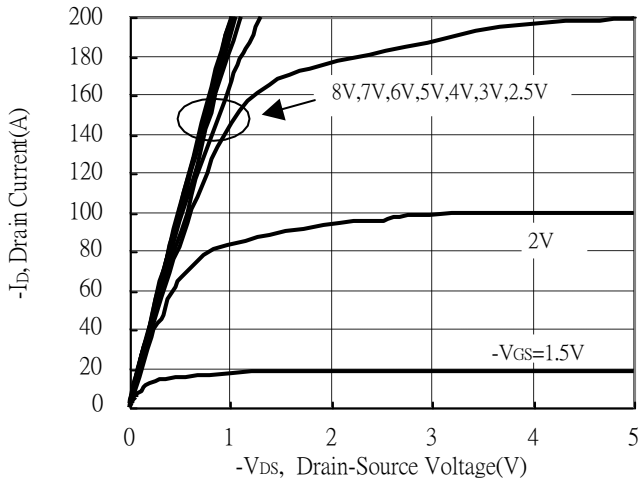
Recommended Soldering Footprint



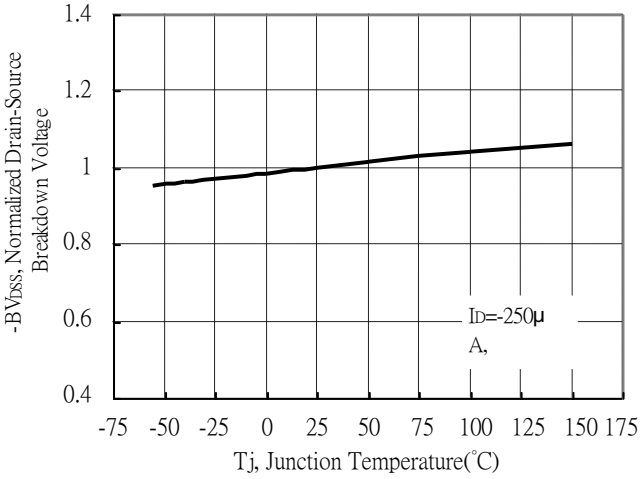
unit : mm

Typical Characteristics

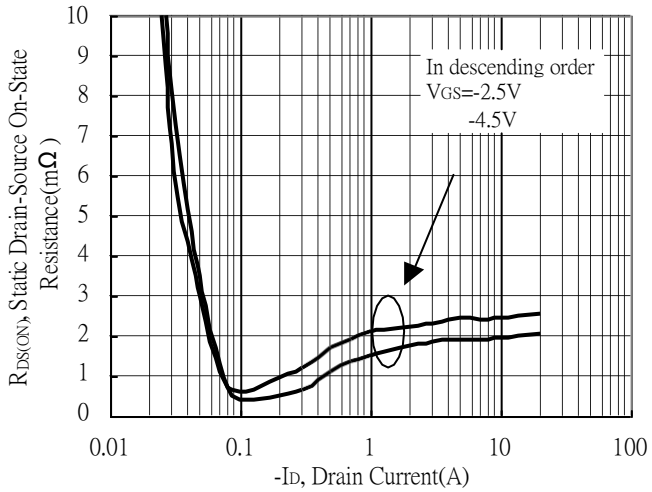
Typical Output Characteristics



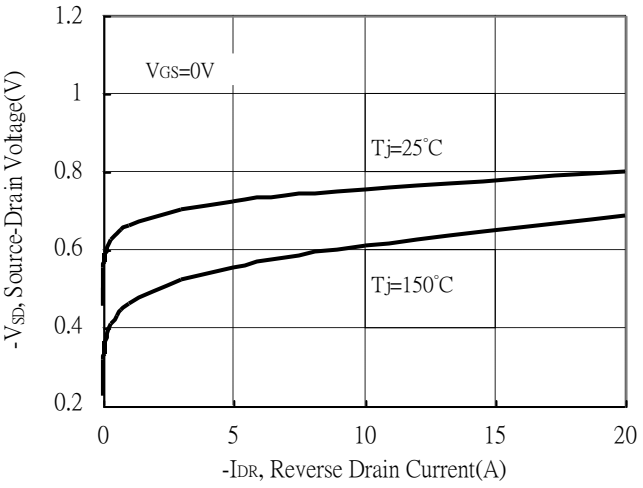
Brekdown Voltage vs Ambient Temperature



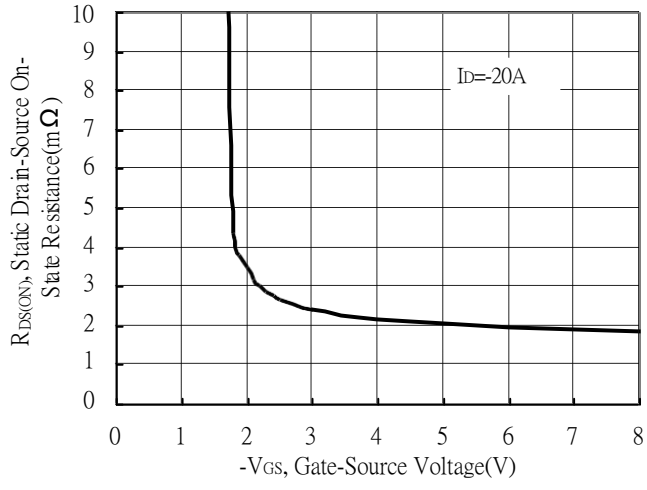
Static Drain-Source On-State resistance vs Drain Current



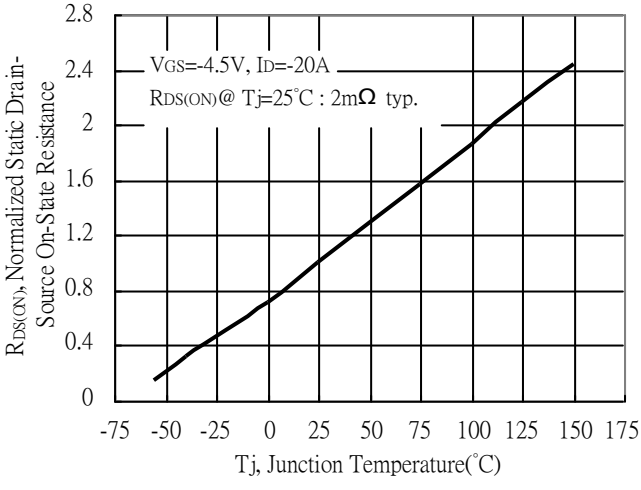
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

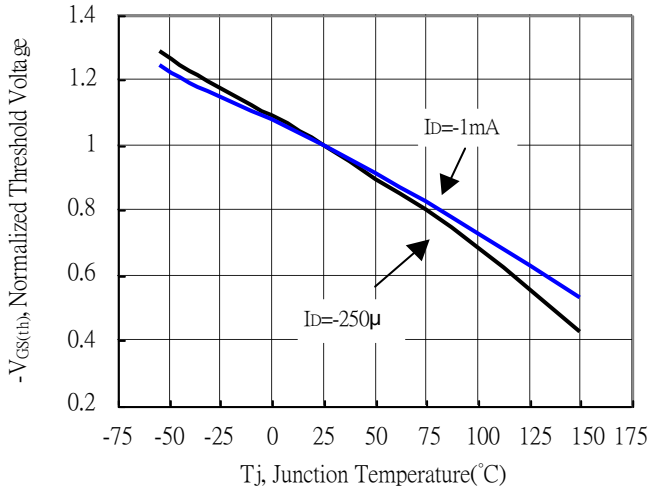


Drain-Source On-State Resistance vs Junction Tempearture

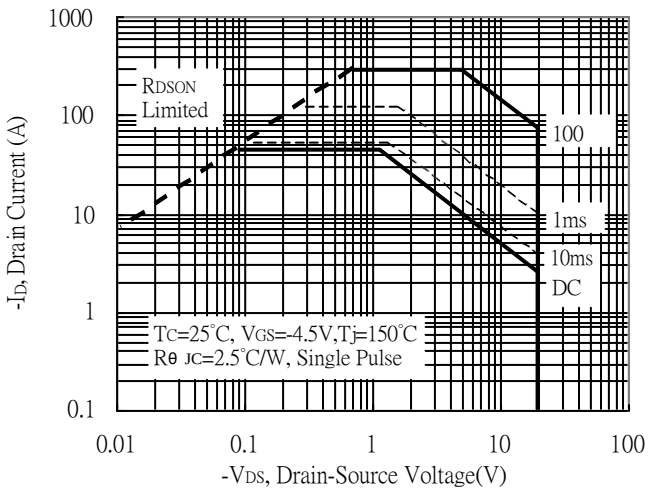


Typical Characteristics(Cont.)

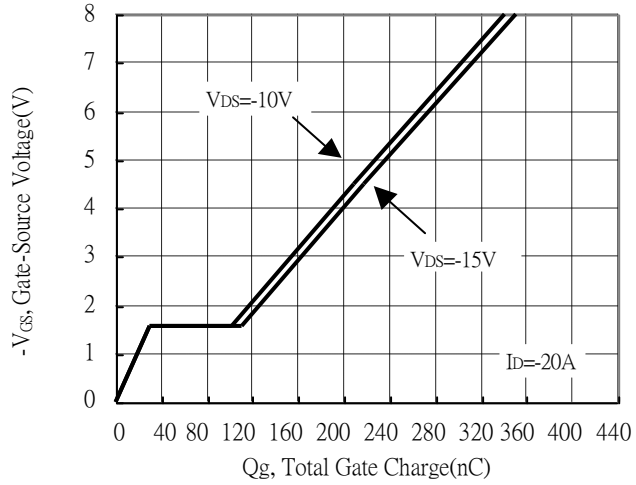
Threshold Voltage vs Junction Tempearture



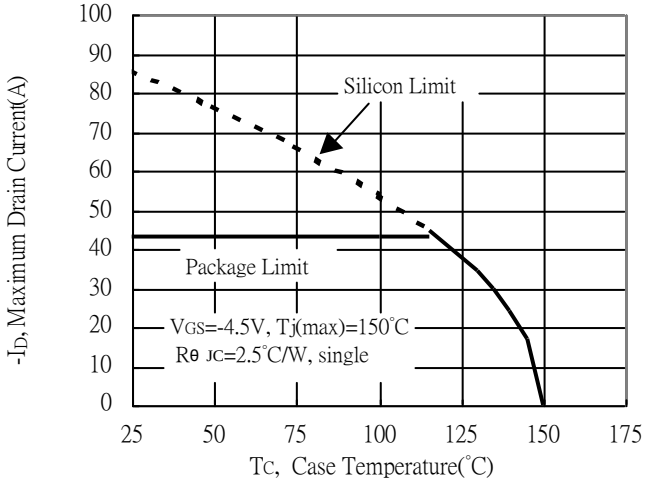
Maximum Safe Operating Area



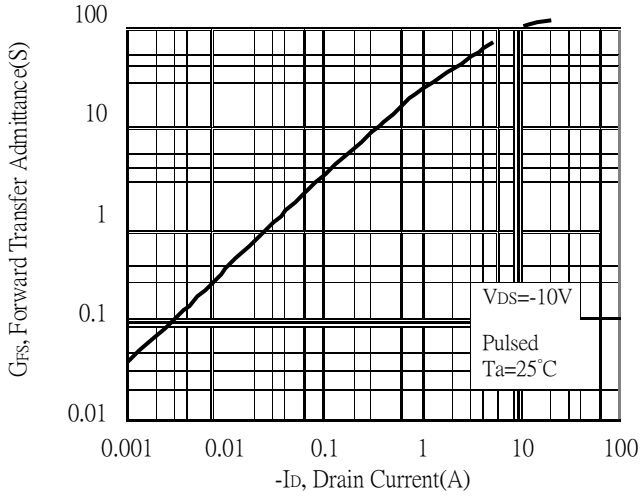
Gate Charge Characteristics



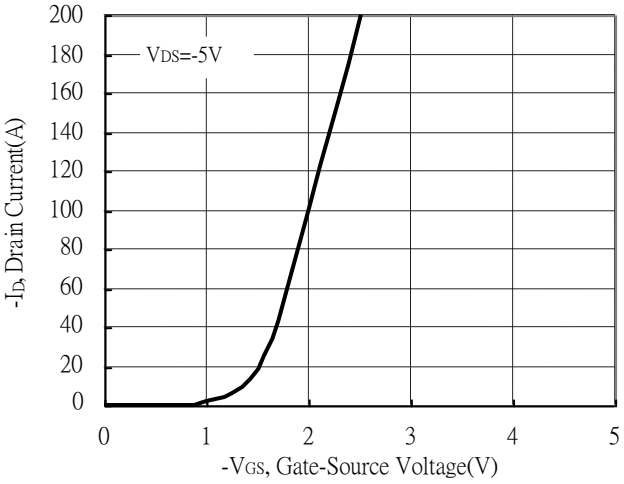
Maximum Drain Current vs Case Temperature



Forward Transfer Admittance vs Drain Current

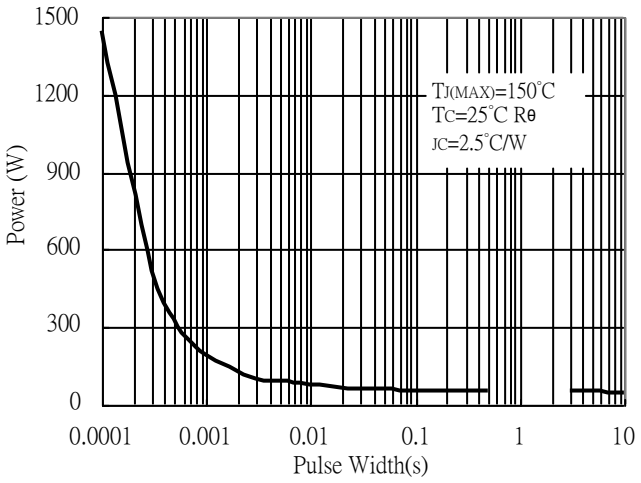


Typical Transfer Characteristics

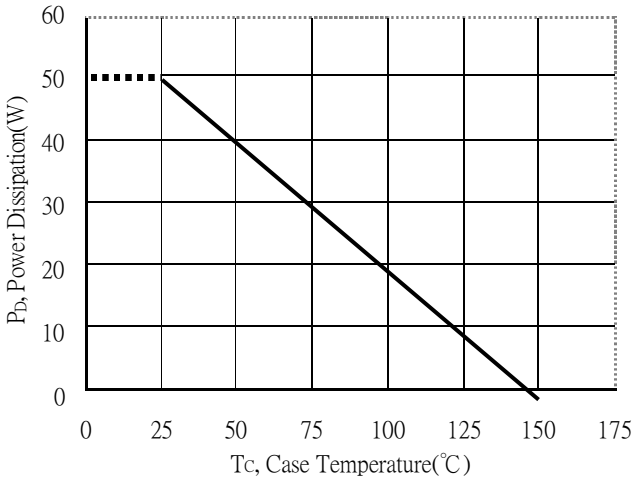


Typical Characteristics(Cont.)

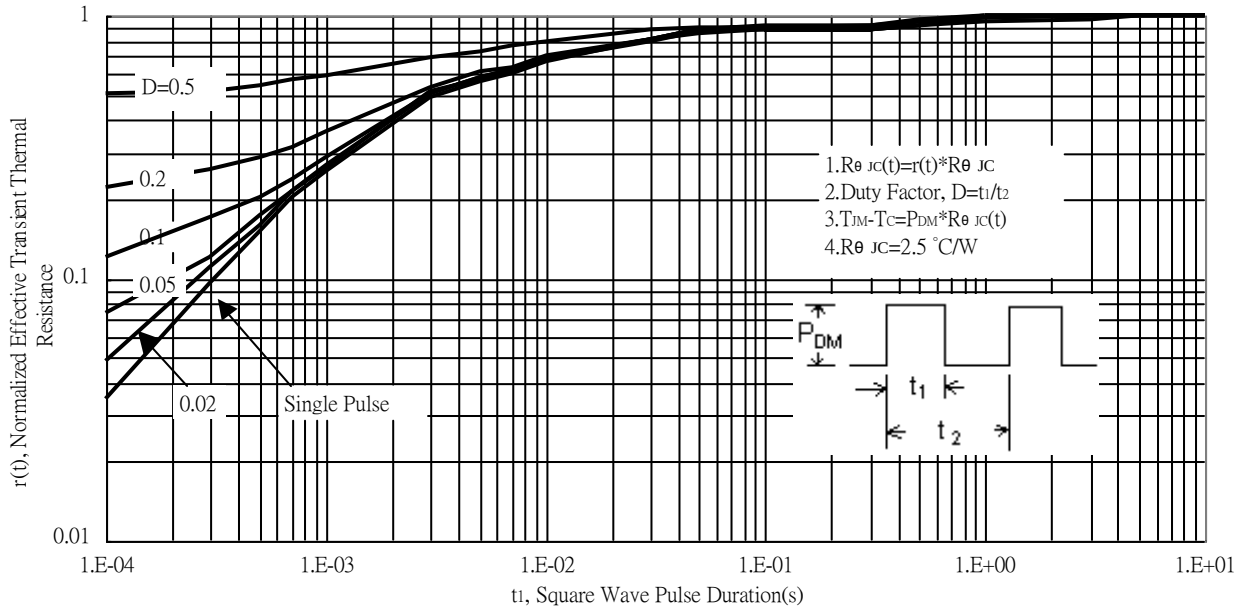
Single Pulse Maximum Power Dissipation



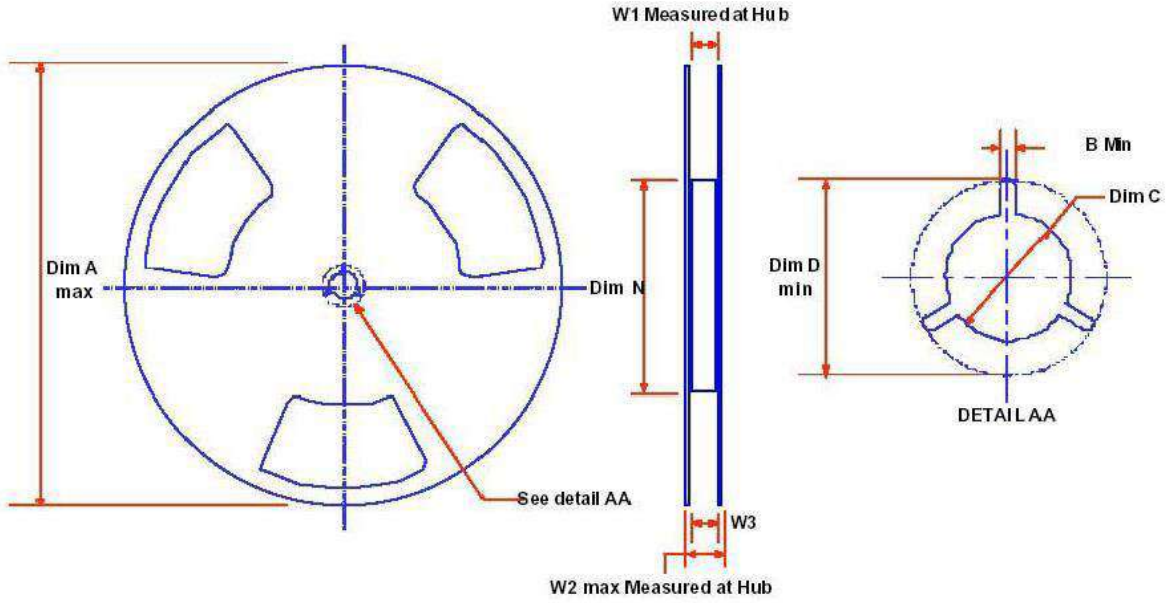
Power Derating Curve



Transient Thermal Response Curves



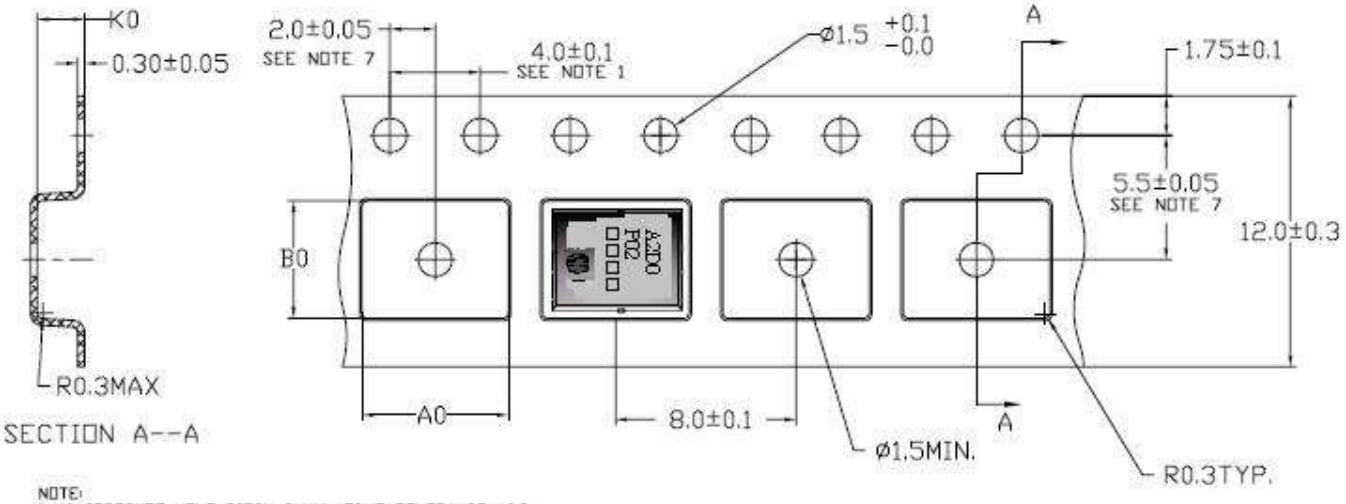
Reel Dimension



Dimensions are in inches and millimeters

Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	13" Dia (STD/L99Z)	13.00 330+/-1	0.059 1.5 Min.	0.512 13.0 Min.	0.795 20.2(ref.)	7.00 178+0/-2	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4(ref.)	0.469 – 0.606 11.9 – 15.4

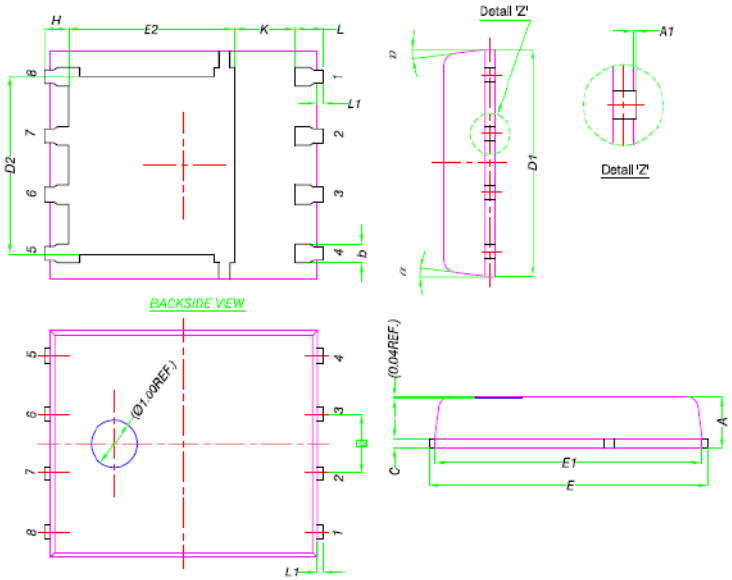
Carrier Tape Dimension



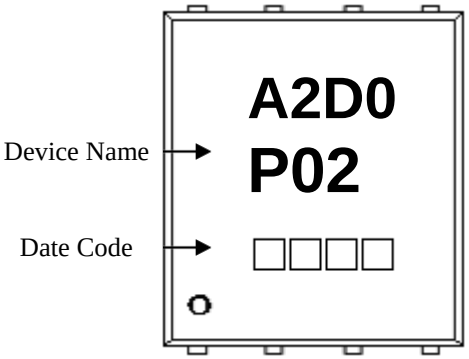
NOTE:
1. 10 SPROCKET HOLE PITCH CUMULATIVE TOLERANCE ±0.2
2. CAMBER NOT TO EXCEED 1mm IN 100mm, NONCUMULATIVE OVER 250mm.
3. MATERIAL: BLACK STATIC DISSIPATIVE PS.(POLYSTYRENE)
4. ALL DIMENSIONS ARE IN MILLIMETERS (UNLESS OTHERWISE SPECIFIED)
5. A0 AND B0 MEASURED ON A PLANE 0.3mm ABOVE THE BOTTOM OF THE POCKET
6. K0 MEASURED FROM A PLANE ON THE INSIDE BOTTOM OF THE POCKET TO THE TOP SURFACE OF THE CARRIER
7. POCKET POSITION RELATIVE TO SPROCKET HOLE MEASURED AS TRUE POSITION OF POCKET, NOT POCKET HOLE
8. SURFACE RESISTIVITY
   1X10E4~1X10E11 OHMS/SQ
   1X10E4~1X10E6 OHMS/SQ. For Fairchild Only

A0=6.5±0.1
B0=5.3±0.1
K0=1.4±0.1

DFN5×6 Dimension



Marking:



8-Lead DFN5×6 Plastic Package
Package Code : H8

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.90	1.10	0.035	0.043	E2	3.38	3.78	0.133	0.149
A1	0.00	0.05	0.000	0.002	e	1.27 BSC		0.050 BSC	
b	0.33	0.51	0.013	0.020	H	0.41	0.61	0.016	0.024
C	0.20	0.30	0.008	0.012	K	1.10	-	0.043	-
D1	4.80	5.00	0.189	0.197	L	0.51	0.71	0.020	0.028
D2	3.61	3.96	0.142	0.156	L1	0.06	0.20	0.002	0.008
E	5.90	6.10	0.232	0.240	θ	8°	12°	8°	12°
E1	5.70	5.80	0.224	0.228					